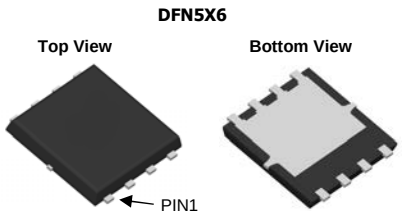
DFN5X6 Plastic-Encapsulate MOSFETS

NJ060N12



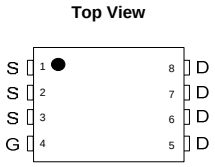
FEATURE

- 120V, 90A

  $R_{DS(ON)}$ Typ = 6.5mΩ @ V_{GS} = 10V

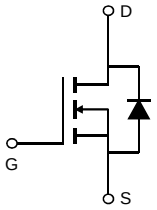
  $R_{DS(ON)}$ Typ = 8.5mΩ @ V_{GS} = 4.5V

- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge



APPLICATION

- Load Switch
- PWM Application
- Power Management



Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		120	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	90	A
		T_C = 100°C	54	A
I_{DM}	Pulsed Drain Current (1)		360	A
E_{AS}	Single Pulsed Avalanche Energy (2)		210	mJ
P_D	Power Dissipation	T_C = 25°C	125	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

MOSFET ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	120	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.4	2	2.6	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 30A	-	6.5	8.5	mΩ
		V_{GS} = 4.5V, I_D = 20A	-	8.5	10.3	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz	-	3478	-	pF
C_{oss}	Output Capacitance		-	1853	-	pF
C_{rss}	Reverse Transfer Capacitance		-	66	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 60V, I_D = 20A	-	40	-	nC
Q_{gs}	Gate Source Charge		-	9	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	10	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 60V I_D= 30A, R_{GEN} = 6Ω	-	13	-	ns
t_r	Turn-On Rise Time		-	25	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	38	-	ns
t_f	Turn-Off Fall Time		-	34	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	90	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	360	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 15A, di/dt = 100A/us	-	65	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	70	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=60V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=29A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Characteristics (T_J = 25℃, unless otherwise specified)

Test Circuit

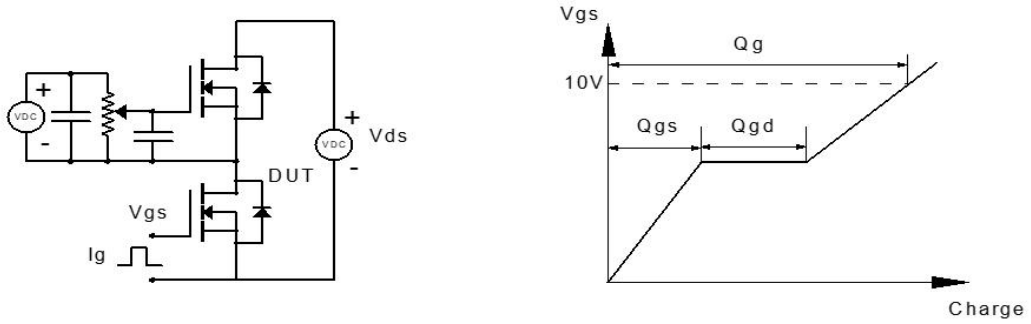


Figure 1: Gate Charge Test Circuit & Waveform

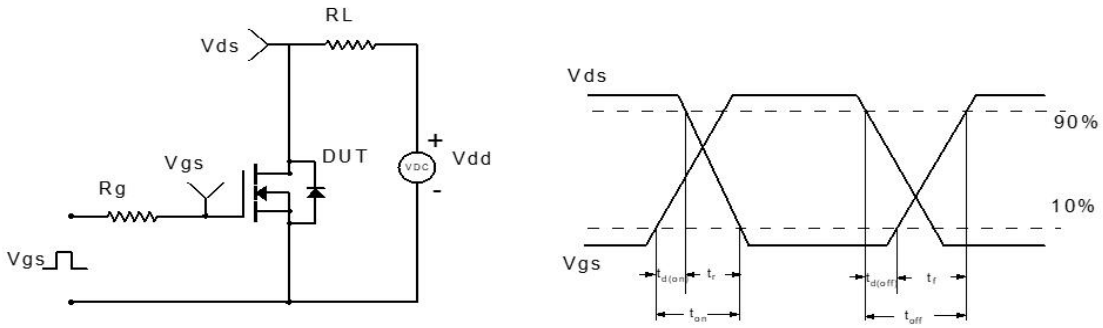


Figure 2: Resistive Switching Test Circuit & Waveform

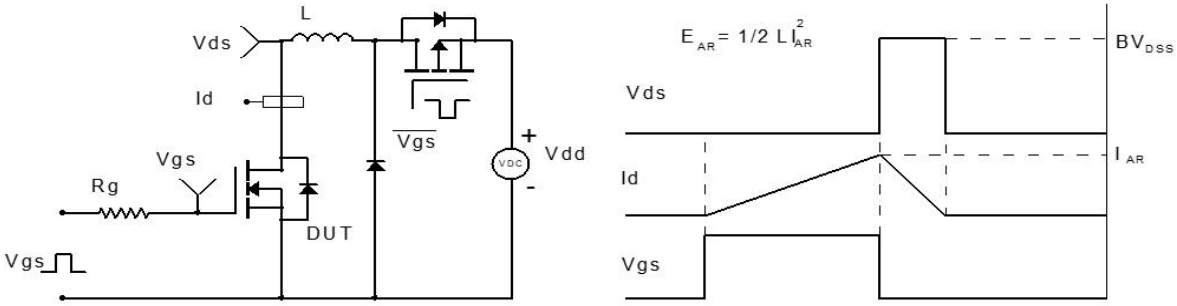


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

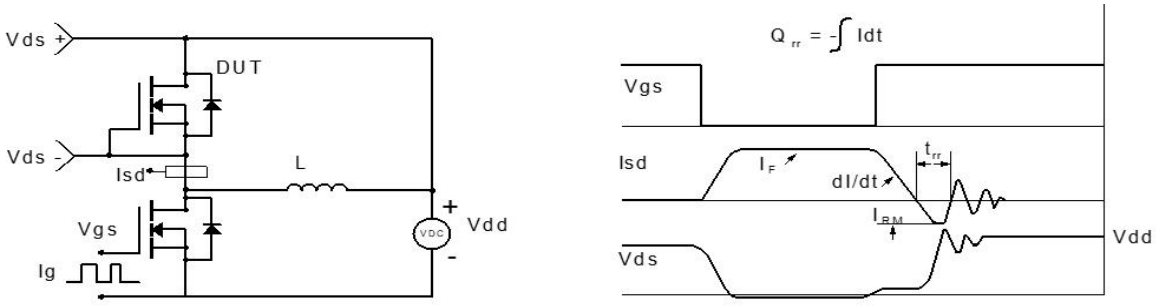
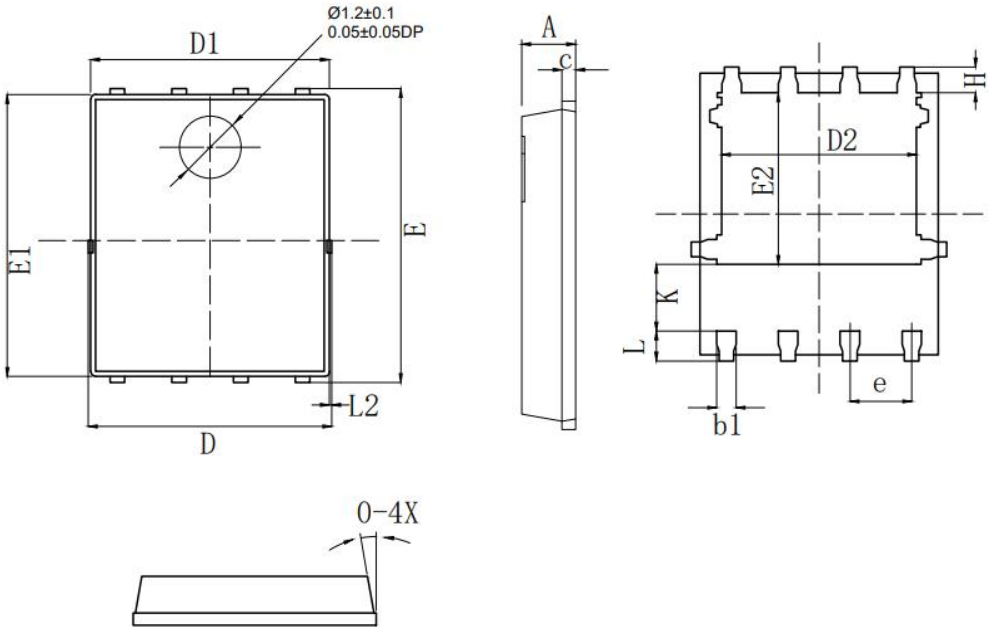


Figure 4: Diode Recovery Test Circuit & Waveform

PDFN5x6-8L



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.30	0.35
b1	0.30	0.40	0.45
c	0.22	0.25	0.28
D	——	——	5.30
D1	4.90	5.05	5.20
D2	3.90REF		
E	6.00	6.15	6.30
E1	5.70	5.85	6.00
E2	3.50REF		
e	1.10	1.27	1.40
H	0.51	0.61	0.71
K	1.10	——	——
L	0.51	0.61	0.71
L2	——	——	0.10
Φ	8°	——	12°